Rigaku

The World Leader in Film Thickness Measurement for Advanced Devices

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For a wide thickness range of metal and oxide/nitride films from nm to μm.

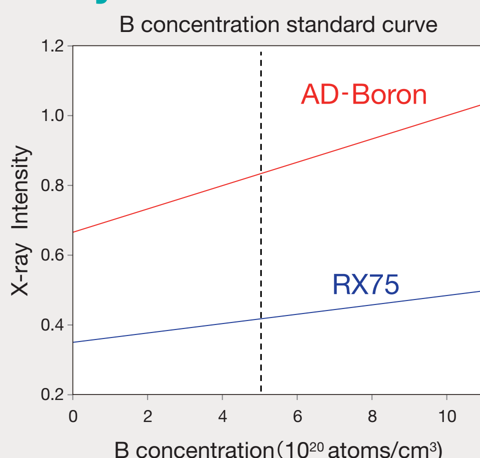
Fully-automated model for in-line HVM use

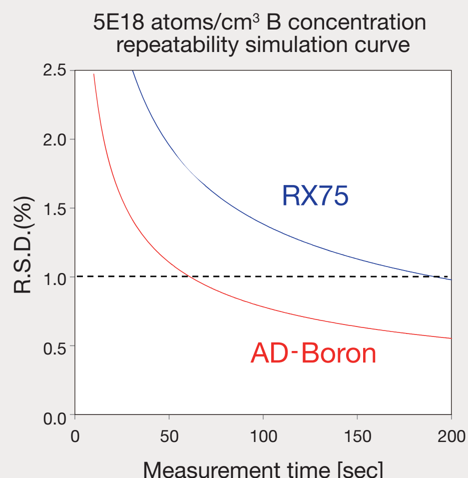
- Dual FOUP load ports
- "Autocal" for automatic calibration
- Host communication based on GEM300
- Mapping measurements

For 200 mm & 300 mm wafer

Boron concentration analysis

AD-Boron channels offer higher sensitivity and higher throughput than standard B channels (RX75).





Various application examples

【Insulation film】

Insulation film : PSG, BPSG

Low-k film : AsSG, FSG, SiOC etc.

Nitride film : Si_3N_4, SiON etc.

High-k film : La_2O_3, HfO_2, Ta_2O_3, Al_2O_3 etc.

【Metal film】

Multi element film : PZT, AlSiCu, AlCu, TiW, TaAl etc.

Single element film : W, Mo, Ti, Co, Al, Cu, Ir, Pt, Ru etc.

Silicide film : WSix, MoSix, TiSix, CoSix, NiSix etc.

Nitride film : TiN, TaN, WN etc.

【Others】

Power Device : Ag/Ni/Ti

Memory : MRAM(MgO, CoFeB), PZT, GST etc.

Impurities : F, S, Cl, Ar